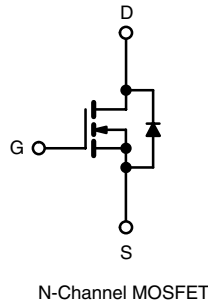
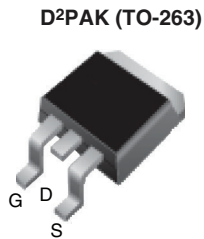


Power MOSFET

PRODUCT SUMMARY	
V _{DS} (V)	500
R _{DS(on)} (Ω)	V _{GS} = 10 V 0.52
Q _g (Max.) (nC)	52
Q _{gs} (nC)	13
Q _{gd} (nC)	18
Configuration	Single



FEATURES

- Low Gate Charge Q_g results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Effective C_{oss} Specified
- Lead (Pb)-free Available



RoHS*
COMPLIANT

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply
- High Speed Power Switching

TYPICAL SMPS TOPOLOGIES

- Two Transistor Forward
- Half and Full Bridge
- Power Factor Correction Boost

ORDERING INFORMATION			
Package	D ² PAK (TO-263)	D ² PAK (TO-263)	D ² PAK (TO-263)
Lead (Pb)-free	IRFS11N50APbF	IRFS11N50ATRRPbF ^a	IRFS11N50ATRLPbF ^a
	SiHFS11N50A-E3	SiHFS11N50ATR-E3 ^a	SiHFS11N50ATL-E3 ^a
SnPb	IRFS11N50A	-	IRFS11N50ATRL ^a
	SiHFS11N50A	-	SiHFS11N50ATL ^a

Note

a. See device orientation.


ABSOLUTE MAXIMUM RATINGS T _C = 25 °C, unless otherwise noted					
PARAMETER			SYMBOL	LIMIT	UNIT
Gate-Source Voltage			V _{GS}	± 30	V
Continuous Drain Current	V _{GS} at 10 V	T _C = 25 °C	I _D	11	A
		T _C = 100 °C		7.0	
Pulsed Drain Current ^a			I _{DM}	44	
Linear Derating Factor				1.3	W/°C
Single Pulse Avalanche Energy ^b			E _{AS}	275	mJ
Repetitive Avalanche Current ^a			I _{AR}	11	A
Repetitive Avalanche Energy ^a			E _{AR}	17	mJ
Maximum Power Dissipation	T _C = 25 °C		P _D	170	W
Peak Diode Recovery dV/dt ^c			dV/dt	6.9	V/ns
Operating Junction and Storage Temperature Range			T _J , T _{stg}	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)	for 10 s			300 ^d	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Starting T_J = 25 °C, L = 4.5 mH, R_G = 25 Ω, I_{AS} = 11 A (see fig. 12).
- I_{SD} ≤ 11 A, di/dt ≤ 140 A/μs, V_{DD} ≤ V_{DS}, T_J ≤ 150 °C.
- 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.75	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	0.50	-	
Maximum Junction-to-Ambient	R_{thJA}	-	62	

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	500	-	-	V	
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$	-	0.060	-	V/°C	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V	
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30\text{ V}$	-	-	± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$	-	-	25	μA	
		$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	250		
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 6.6\text{ A}^b$	-	-	0.52	Ω	
Forward Transconductance	g_{fs}	$V_{DS} = 50\text{ V}, I_D = 6.6\text{ A}$	6.1	-	-	S	
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V},$ $V_{DS} = 25\text{ V},$ $f = 1.0\text{ MHz}$, see fig. 5	-	1423	-	pF	
Output Capacitance	C_{oss}		-	208	-		
Reverse Transfer Capacitance	C_{rss}		-	8.1	-		
Output Capacitance	C_{oss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 1.0\text{ V}, f = 1.0\text{ MHz}$	-	2000	-	
Effective Output Capacitance	$C_{oss\text{ eff.}}$		$V_{DS} = 400\text{ V}, f = 1.0\text{ MHz}$	-	55	-	
			$V_{DS} = 0\text{ V to } 400\text{ V}^c$	-	97	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 11\text{ A}, V_{DS} = 400\text{ V}$ see fig. 6 and 13 ^b	-	-	52	nC
Gate-Source Charge	Q_{gs}			-	-	13	
Gate-Drain Charge	Q_{gd}			-	-	18	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 250\text{ V}, I_D = 11\text{ A}$ $R_G = 9.1\text{ }\Omega, R_D = 22\text{ }\Omega,$ see fig. 10 ^b	-	14	-	ns	
Rise Time	t_r		-	35	-		
Turn-Off Delay Time	$t_{d(off)}$		-	32	-		
Fall Time	t_f		-	28	-		
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	11	A	
Pulsed Diode Forward Current ^a	I_{SM}		-	-	44		
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 11\text{ A}, V_{GS} = 0\text{ V}^b$	-	-	1.5	V	
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = 11\text{ A}, di/dt = 100\text{ A}/\mu\text{s}^b$	-	510	770	ns	
Body Diode Reverse Recovery Charge	Q_{rr}		-	3.4	5.1	μC	
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.
- $C_{oss\text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80 % V_{DS} .

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

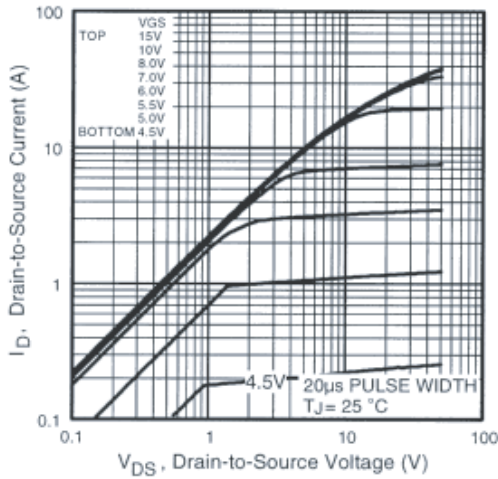


Fig. 1 - Typical Output Characteristics

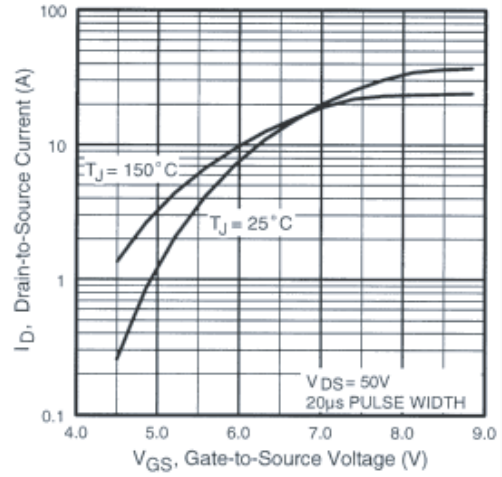


Fig. 3 - Typical Transfer Characteristics

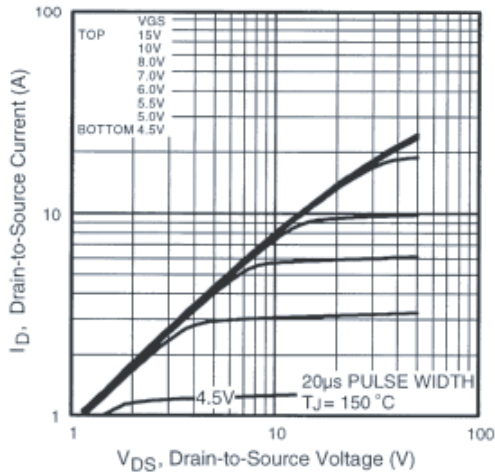


Fig. 2 - Typical Output Characteristics

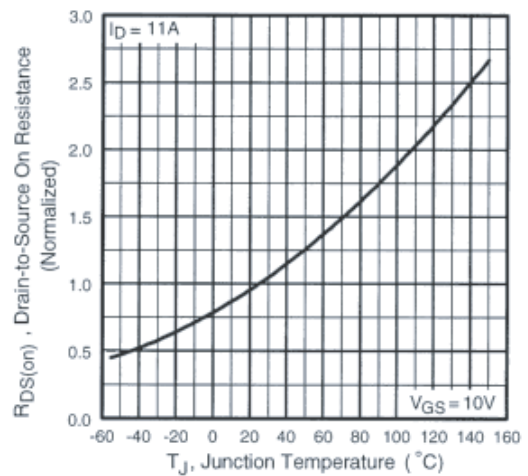


Fig. 4 - Normalized On-Resistance vs. Temperature

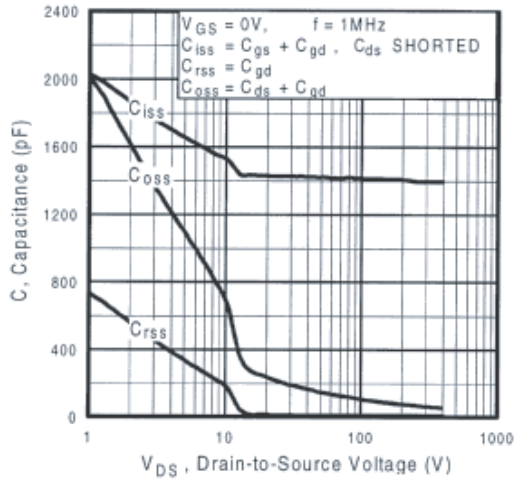


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

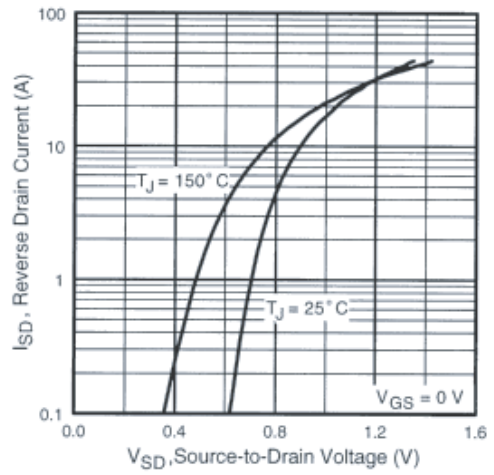


Fig. 7 - Typical Source-Drain Diode Forward Voltage

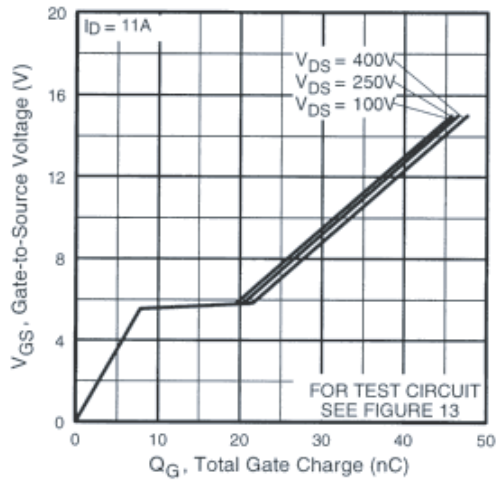


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

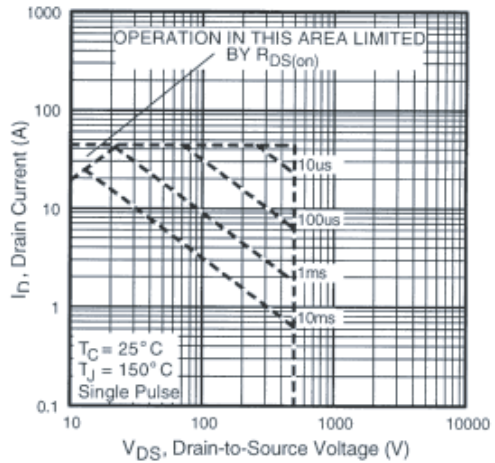


Fig. 8 - Maximum Safe Operating Area

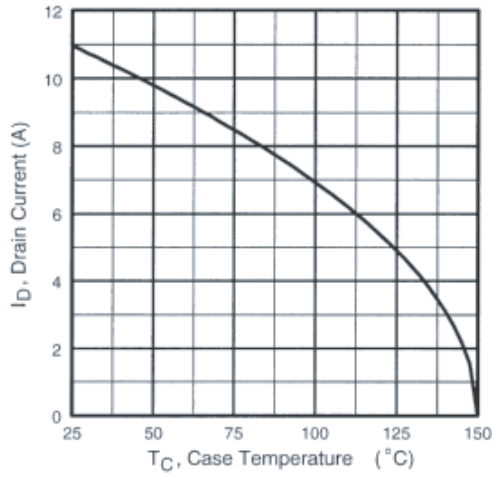


Fig. 9 - Maximum Drain Current vs. Case Temperature

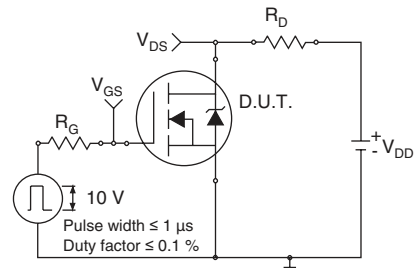


Fig. 10a - Switching Time Test Circuit

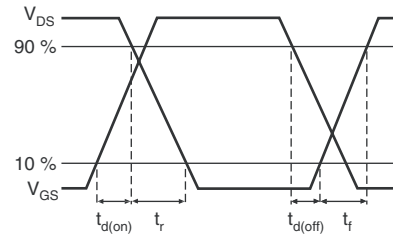


Fig. 10b - Switching Time Waveforms

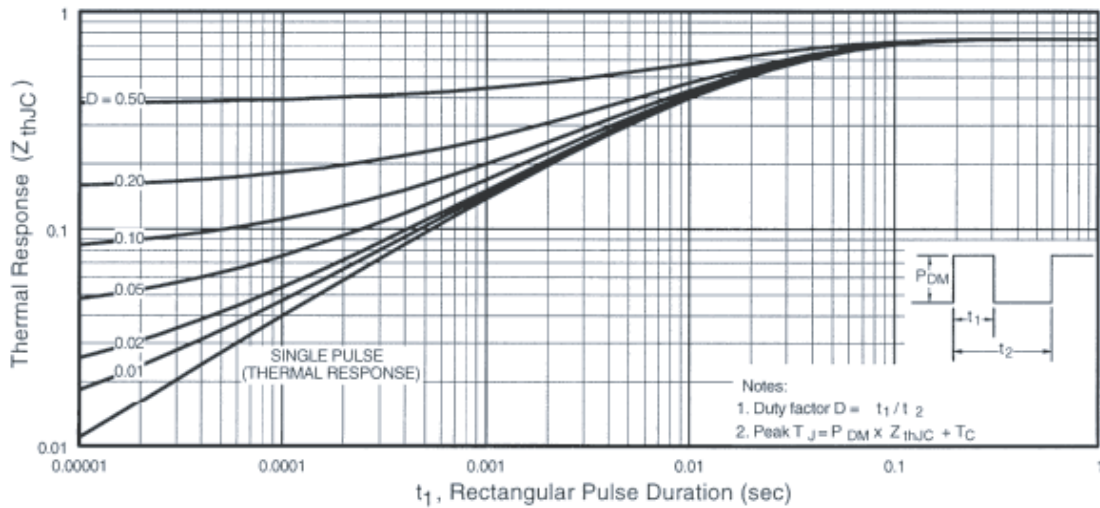


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

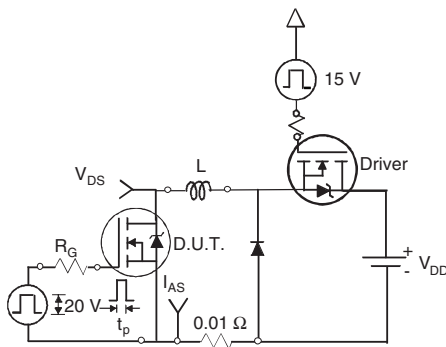


Fig. 12a - Unclamped Inductive Test Circuit

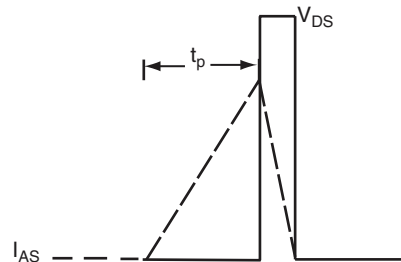


Fig. 12b - Unclamped Inductive Waveforms

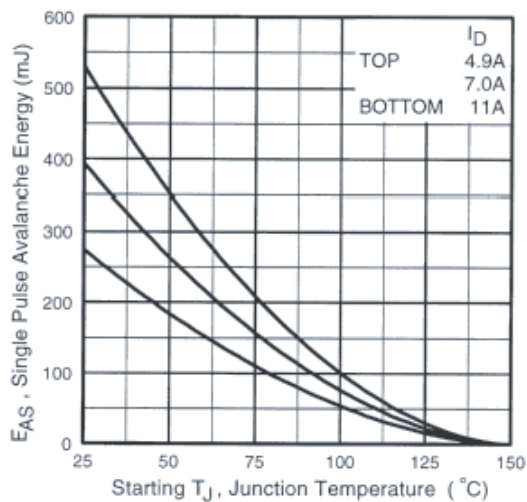


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

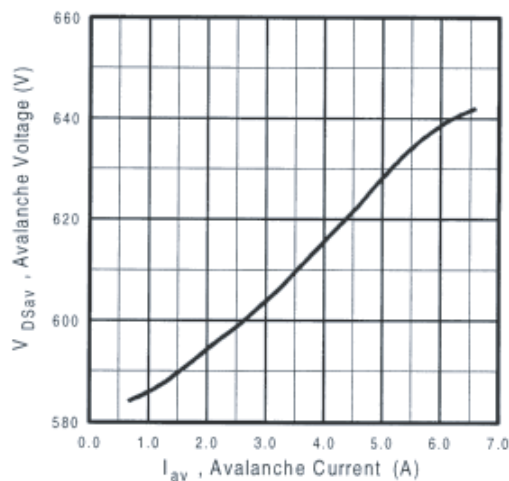


Fig. 12d - Typical Drain-to-Source Voltage vs. Avalanche Current

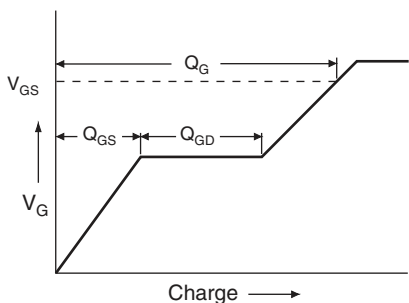


Fig. 13a - Basic Gate Charge Waveform

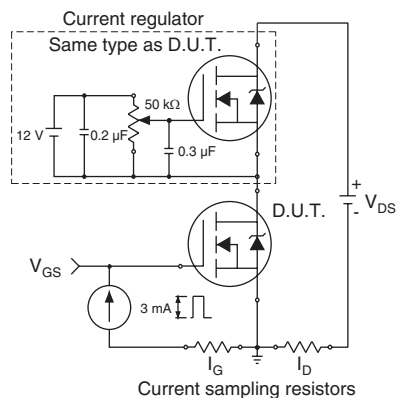
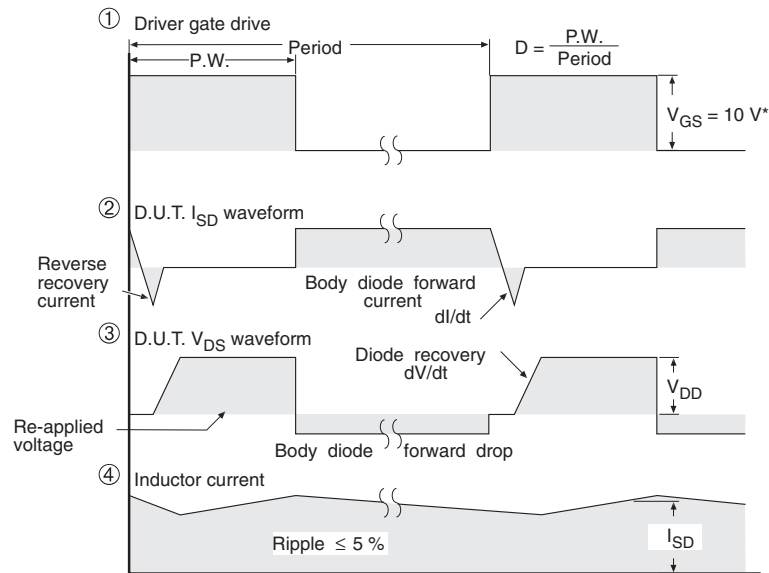
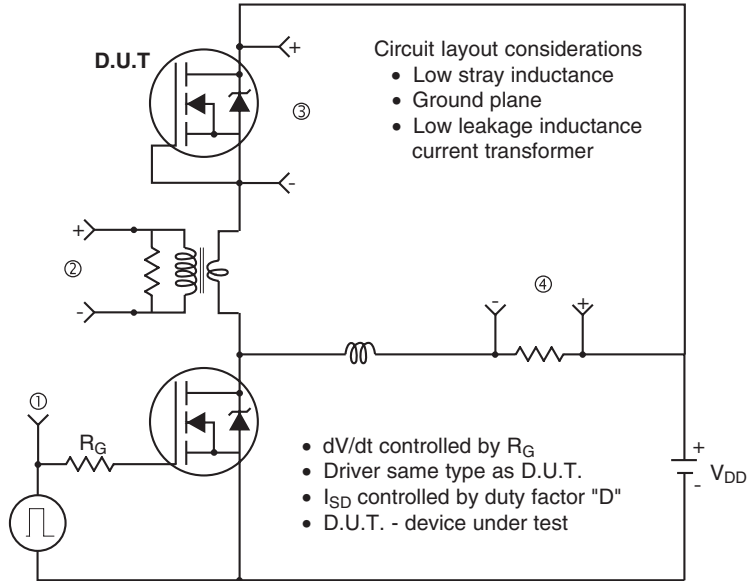


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



* $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel

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